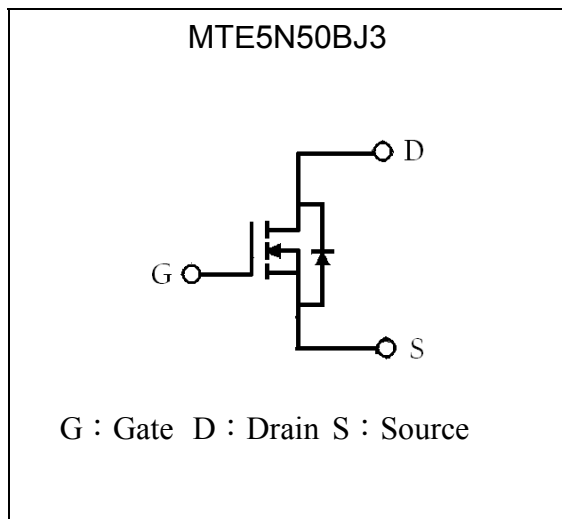
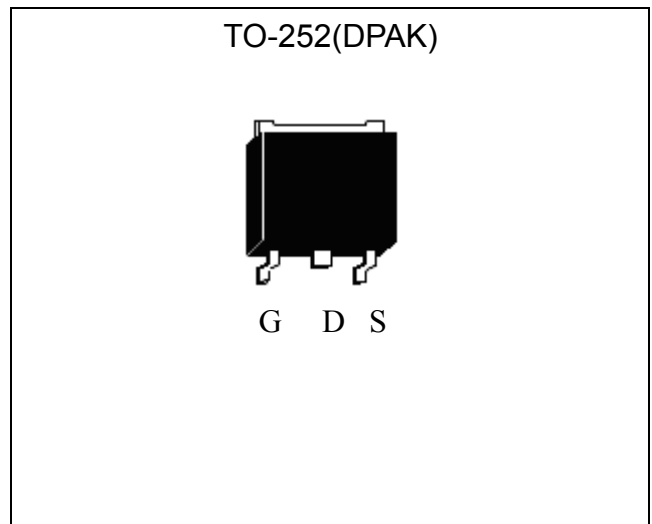


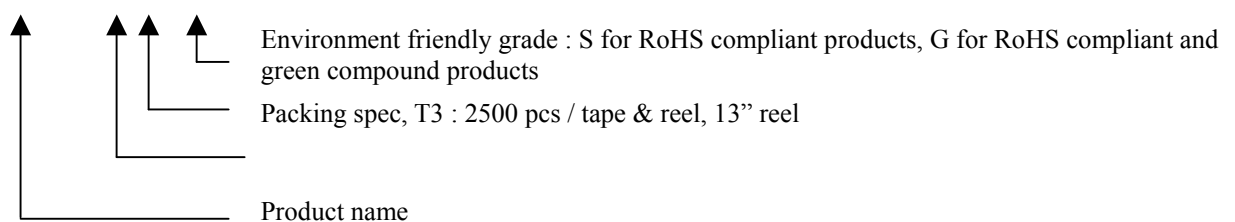
N-Channel Enhancement Mode Power MOSFET**Features**

- Low On Resistance
- Simple Drive Requirement
- Low Gate Charge
- Fast Switching Characteristic
- RoHS compliant package
- Pb-free lead plating and halogen-free package

BV_{DSS}	500V
$I_D @ V_{GS}=10V, T_C=25^{\circ}C$	4.5A
$R_{DS(on)(TYP)} @ V_{GS}=10V, I_D=2.25A$	1.1 Ω

Symbol**Outline****Ordering Information**

Device	Package	Shipping
MTE5N50BJ3-0-T3-G	TO-252 (Pb-free lead plating and halogen-free package)	2500 pcs / Tape & Reel



Absolute Maximum Ratings (T_C=25°C)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V _{DS}	500	V
Gate-Source Voltage	V _{GS}	±30	
Continuous Drain Current @T _C =25°C, V _{GS} =10V	I _D	4.5	A
Continuous Drain Current @T _C =100°C, V _{GS} =10V		2.8	
Pulsed Drain Current (Note 1)	I _{DM}	18	
Single Pulse Avalanche Energy (Note 2)	E _{AS}	90	mJ
Avalanche Current (Note 1)	I _{AS}	4.5	A
Repetitive Avalanche Energy (Note 1)	E _{AR}	4.8	mJ
Maximum Temperature for Soldering @ Lead at 0.125 in(0.318mm) from case for 10 seconds	T _L	300	°C
Total Power Dissipation (T _A =25°C) (Note 4)	P _D	2	W
Total Power Dissipation (T _C =25°C)		48	W
Linear Derating Factor		0.38	W/°C
Operating Junction and Storage Temperature	T _j , T _{stg}	-55~+150	°C

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	R _{th,j-c}	2.6	°C/W
Thermal Resistance, Junction-to-ambient, max (Note 4)	R _{th,j-a}	50	
Thermal Resistance, Junction-to-ambient, max		110	

Note : 1.Repetitive rating; pulse width limited by maximum junction temperature.

2. I_{AS}=4.5A, V_{DD}=50V, L=8mH, R_G=25Ω, starting T_J=+25°C.

3. I_{SD}≤4.5A, dI/dt≤100A/μs, V_{DD}≤BV_{DSS}, starting T_J=+25°C.

4. When the device is mounted on 1 in² FR-4 board with 2 oz. copper, in a still air environment with T_A=25°C.

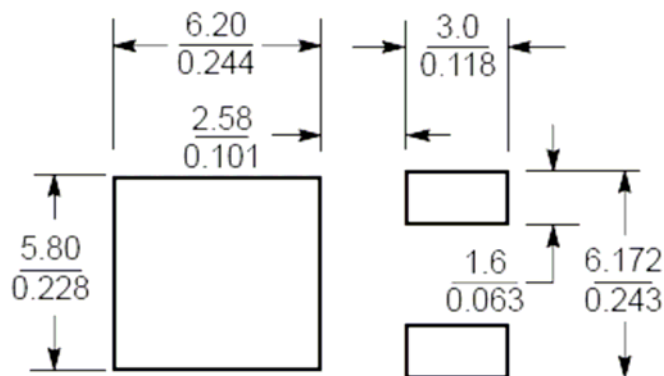
Characteristics (T_C=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	500	-	-	V	V _{GS} =0V, I _D =250μA, T _J =25°C
ΔBV _{DSS} /ΔT _J	-	0.6	-	V/°C	Reference to 25°C, I _D =250μA
V _{GS(th)}	2.0	-	4.0	V	V _{DS} = V _{GS} , I _D =250μA
*G _{FS}	-	5	-	S	V _{DS} =15V, I _D =2.25A
I _{GSS}	-	-	±100	nA	V _{GS} =±30V
I _{DSS}	-	-	1	μA	V _{DS} =500V, V _{GS} =0V
	-	-	10		V _{DS} =400V, V _{GS} =0V, T _C =125°C
*R _{DS(ON)}	-	1.1	1.5	Ω	V _{GS} =10V, I _D =2.25A
Dynamic					
*Q _g	-	17.4	-	nC	I _D =4.5A, V _{DD} =400V, V _{GS} =10V
*Q _{gs}	-	3.4	-		
*Q _{gd}	-	7.6	-		

*t _{d(ON)}	-	10.6	-	ns	V _{DD} =250V, I _D =4.5A, V _{GS} =10V, R _G =25 Ω
*t _r	-	10	-		
*t _{d(OFF)}	-	35	-		
*t _f	-	31.2	-		
C _{iss}	-	572	-	pF	V _{GS} =0V, V _{DS} =25V, f=1MHz
C _{oss}	-	65	-		
C _{rss}	-	32	-		
Source-Drain Diode					
*I _S	-	-	4.5	A	
*I _{SM}	-	-	18		
*V _{SD}	-	-	1.5	V	I _S =4.5A, V _{GS} =0V
*t _{rr}	-	260	-	ns	V _{GS} =0, I _F =4.5A, dI _F /dt=100A/μs
*Q _{rr}	-	1.1	-	μC	

*Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

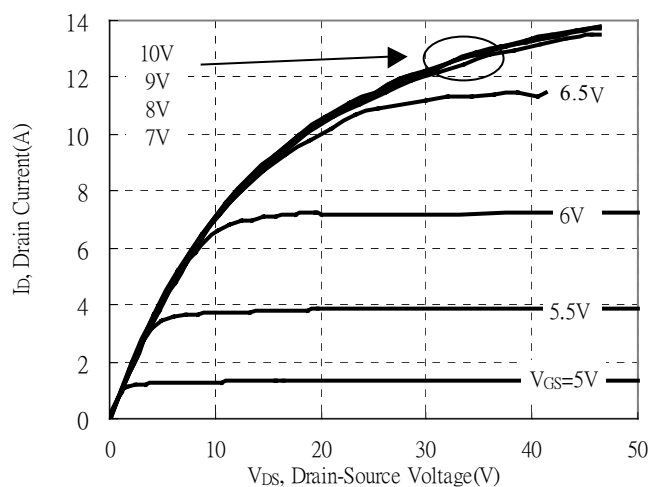
Recommended soldering footprint



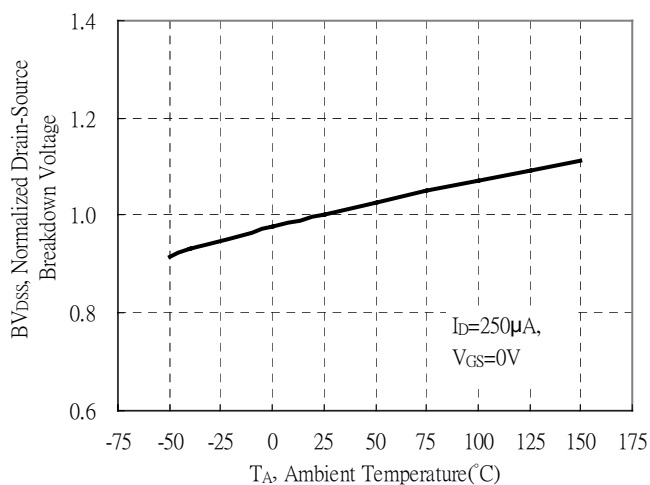
Unit ($\frac{\text{mm}}{\text{inch}}$)

Typical Characteristics

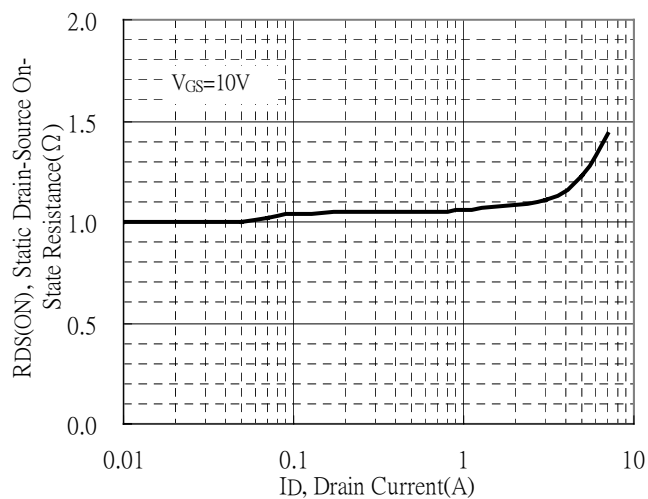
Typical Output Characteristics



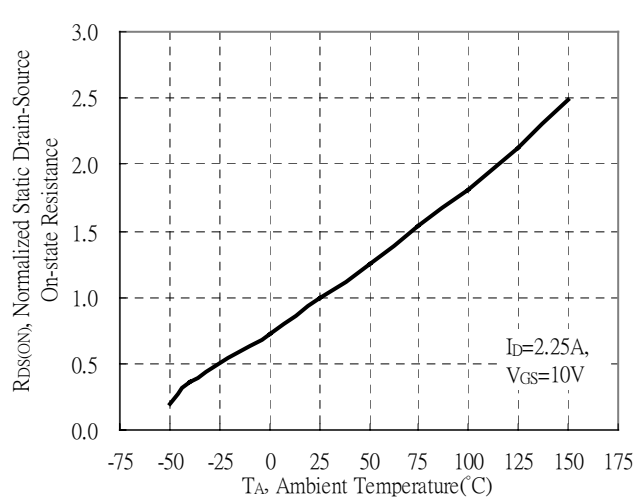
Breakdown Voltage vs Ambient Temperature



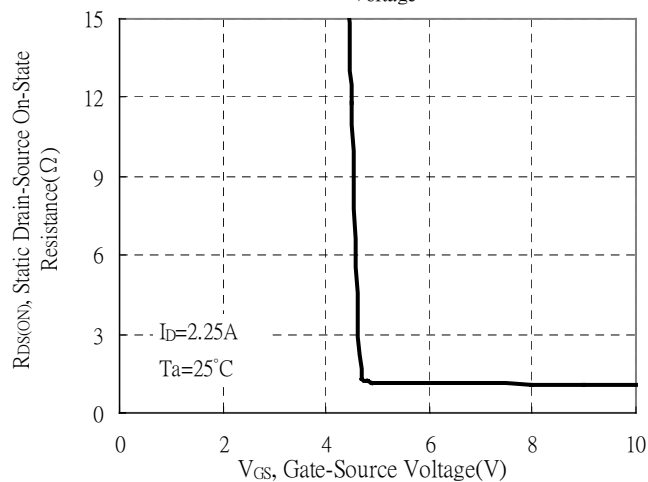
Static Drain-Source On-State resistance vs Drain Current



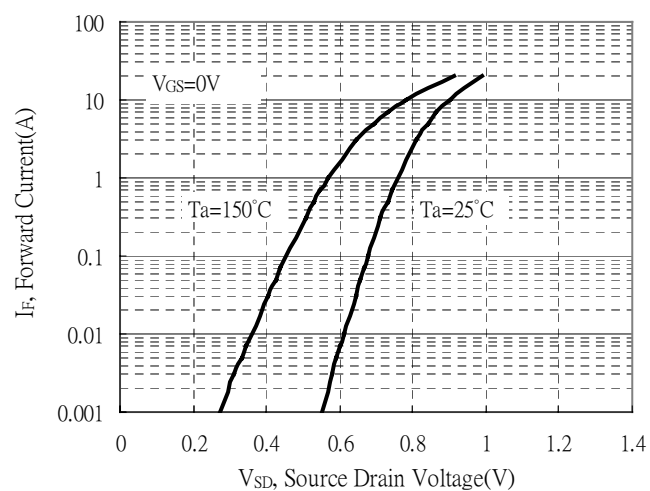
Static Drain-Source On-resistance vs Ambient Temperature



Static Drain-Source On-State Resistance vs Gate-Source Voltage

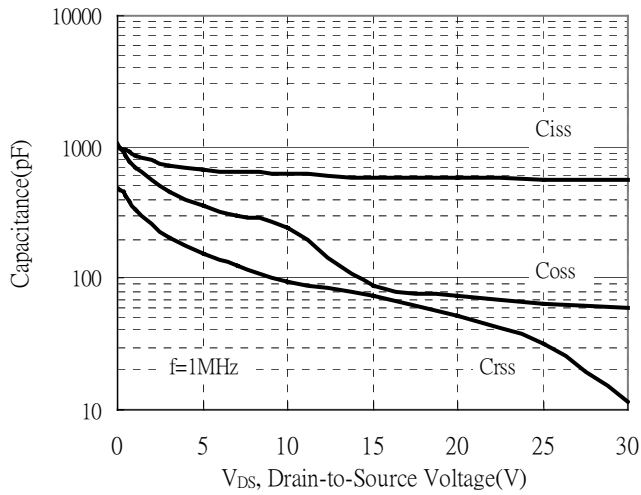


Forward Drain Current vs Source-Drain Voltage

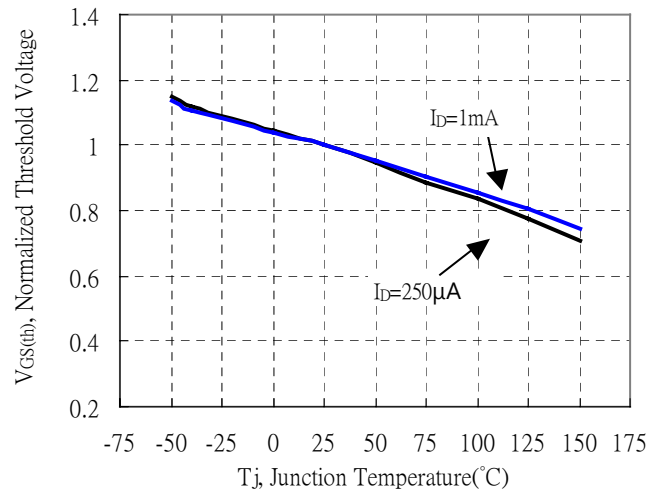


Typical Characteristics(Cont.)

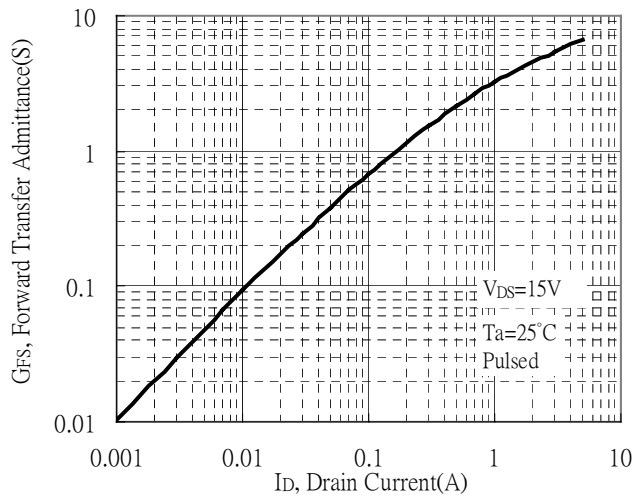
Capacitance vs Reverse Voltage



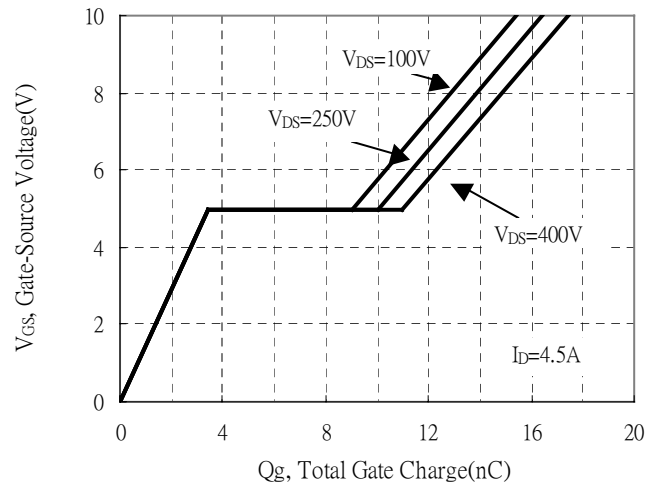
Threshold Voltage vs Junction Temperature



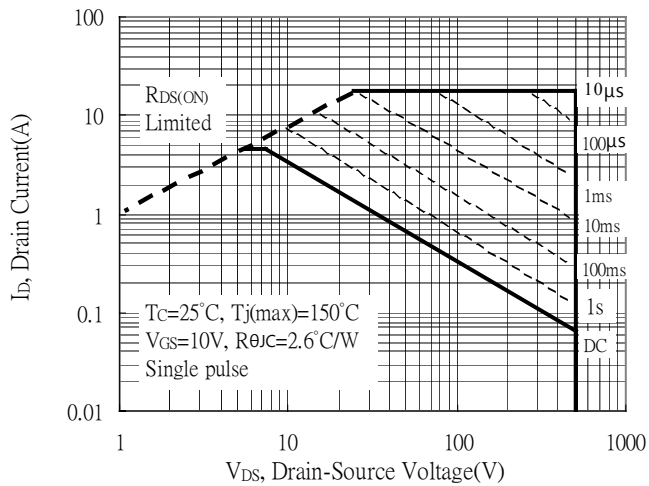
Forward Transfer Admittance vs Drain Current



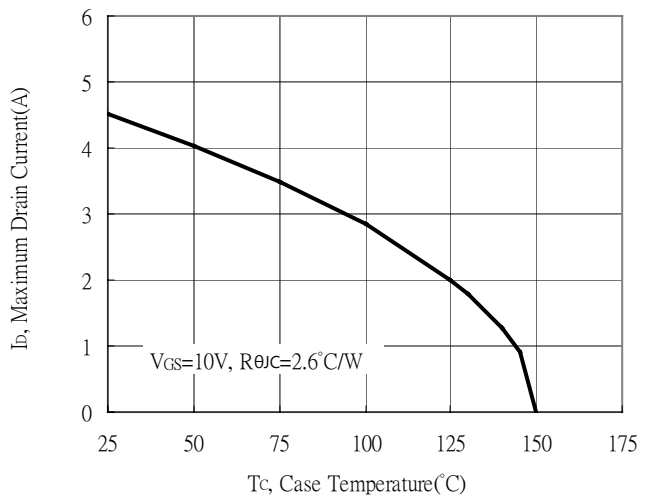
Gate Charge Characteristics



Maximum Safe Operating Area

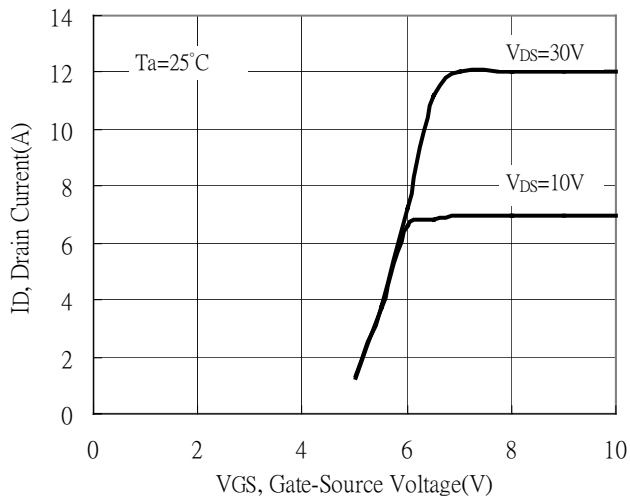


Maximum Drain Current vs Case Temperature

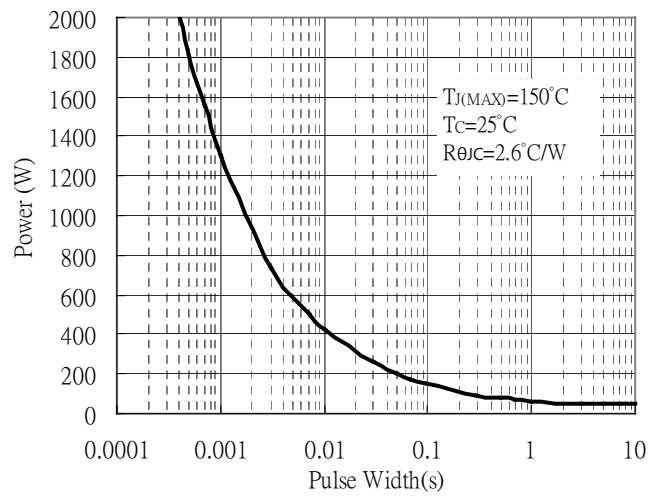


Typical Characteristics(Cont.)

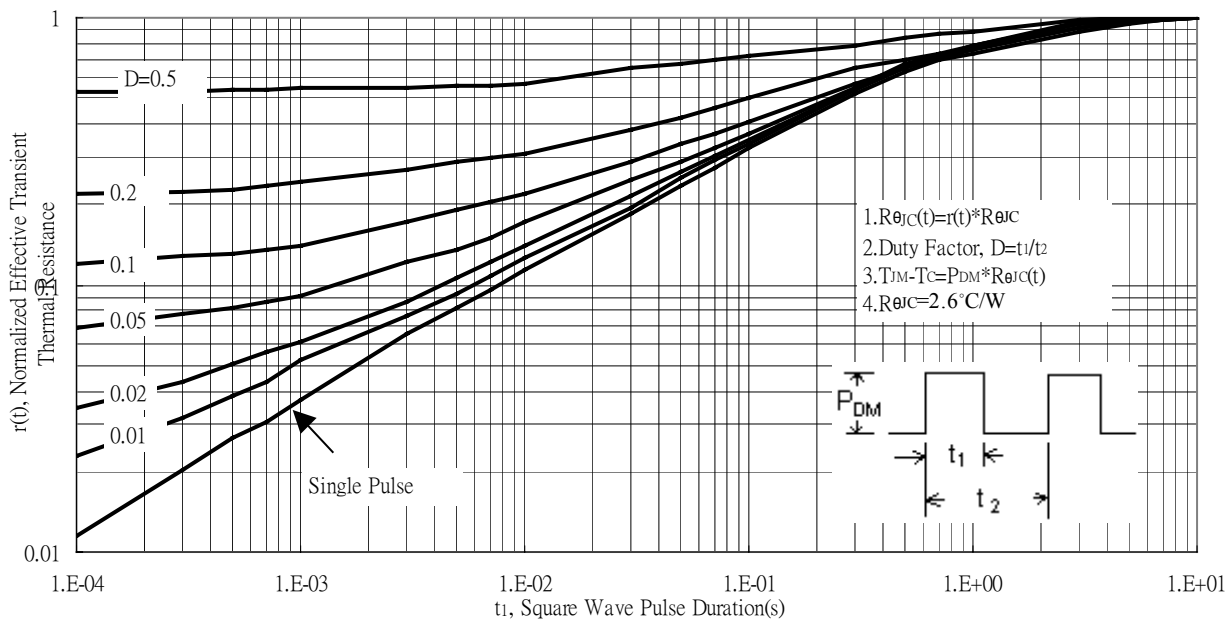
Drain Current vs Gate-Source Voltage



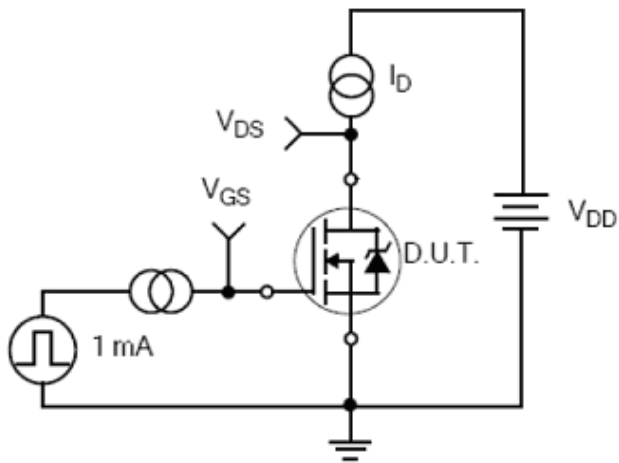
Single Pulse Power Rating, Junction to Case



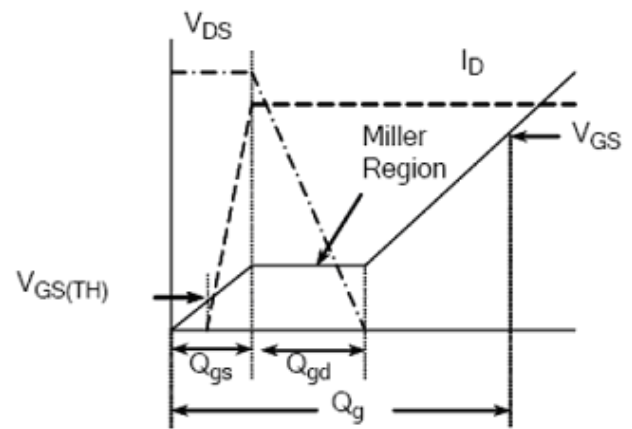
Transient Thermal Response Curves



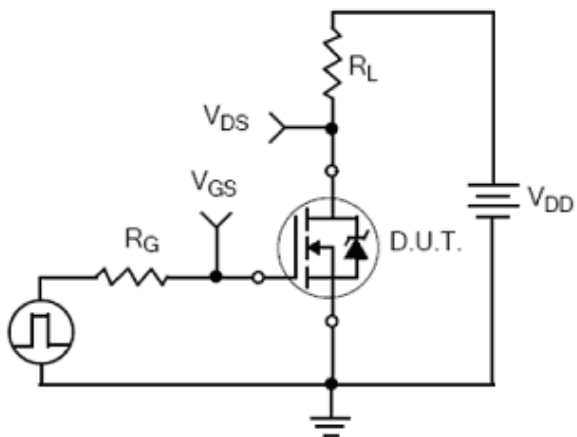
Test Circuit and Waveforms



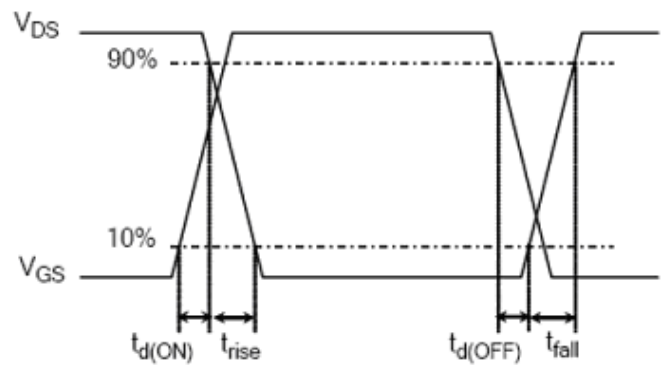
Gate Charge Test Circuit



Gate Charge Waveform



Resistive Switching Test Circuit



Resistive Switching Waveforms

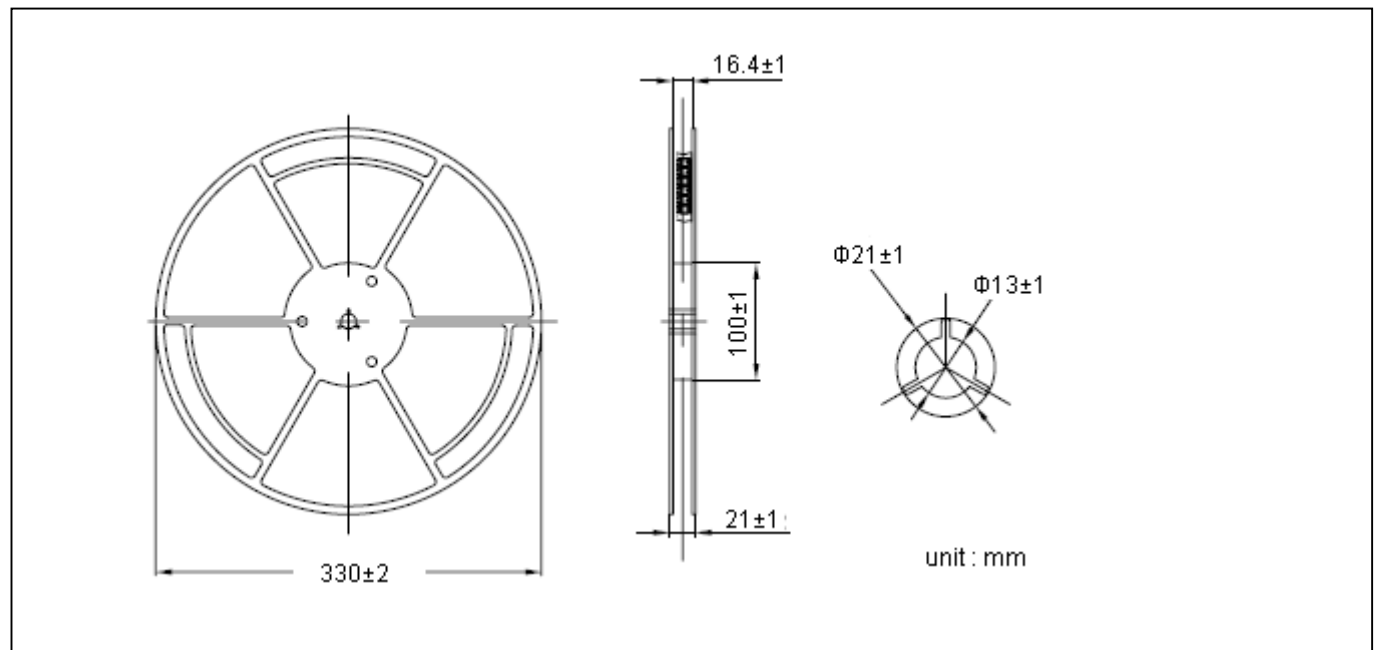
The diagram shows a circuit for testing a Device Under Test (D.U.T.). A current pump, consisting of a MOSFET and a diode, is connected to a double-pulse current source and a di/dt adjustment resistor. The current pump's output is connected to the D.U.T., which is also a MOSFET with a diode. The D.U.T. is connected to an inductor L and a load inductor I_D . The circuit is powered by a V_{DD} supply.

Timing diagram showing the relationship between the gate voltage V_{GS} , the drain current I_{AS} , and the drain-source voltage BV_{DSS} . The gate voltage V_{GS} is a rectangular pulse of duration t_p . The drain current I_{AS} is a triangular pulse that rises linearly from 0 to I_{AS} during the gate pulse and then falls linearly to 0. The average voltage t_{AV} is the time interval during which the drain current is non-zero. The drain-source voltage BV_{DSS} is a rectangular pulse that occurs during the fall time of the drain current.

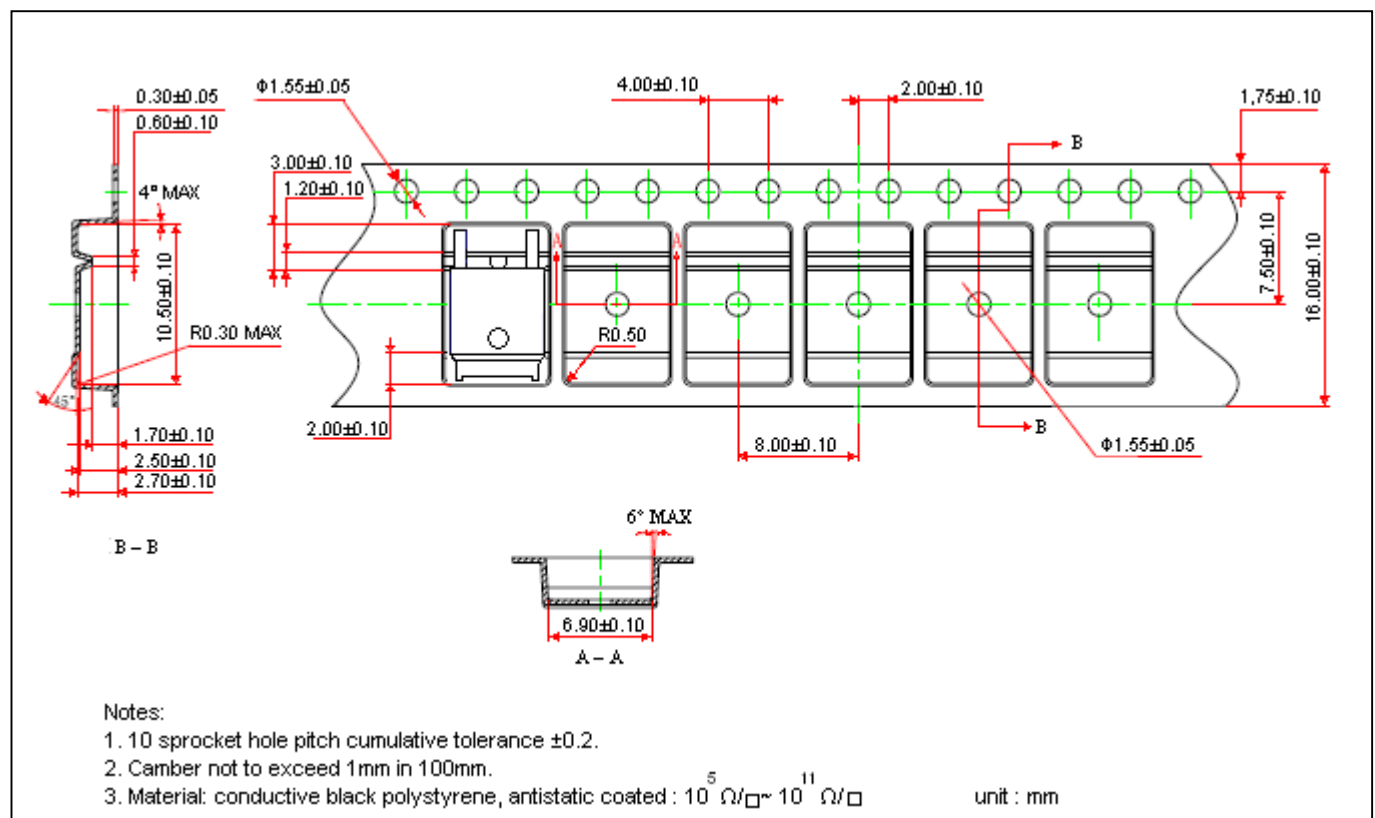
$$E_{AS} = \frac{I_{AS}^2 L}{2}$$

Unclamped Inductive Switching Waveforms

Reel Dimension

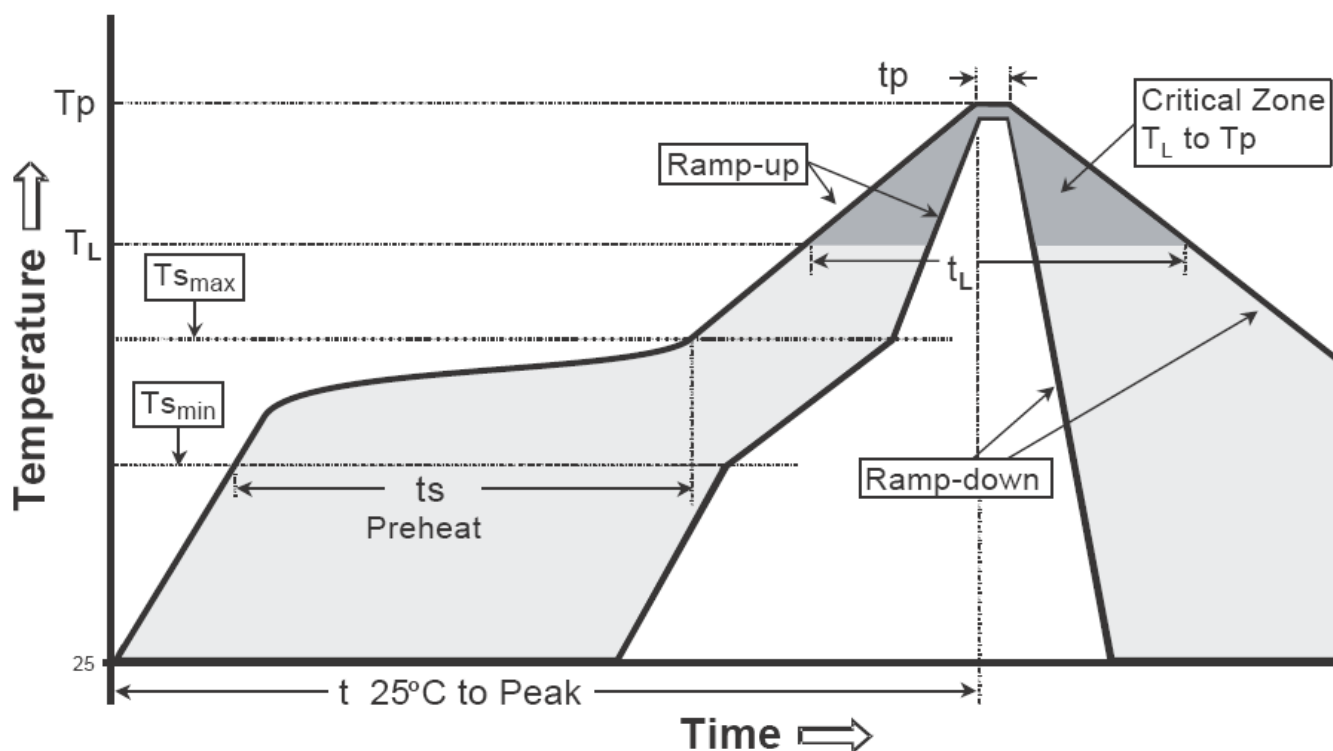


Carrier Tape Dimension



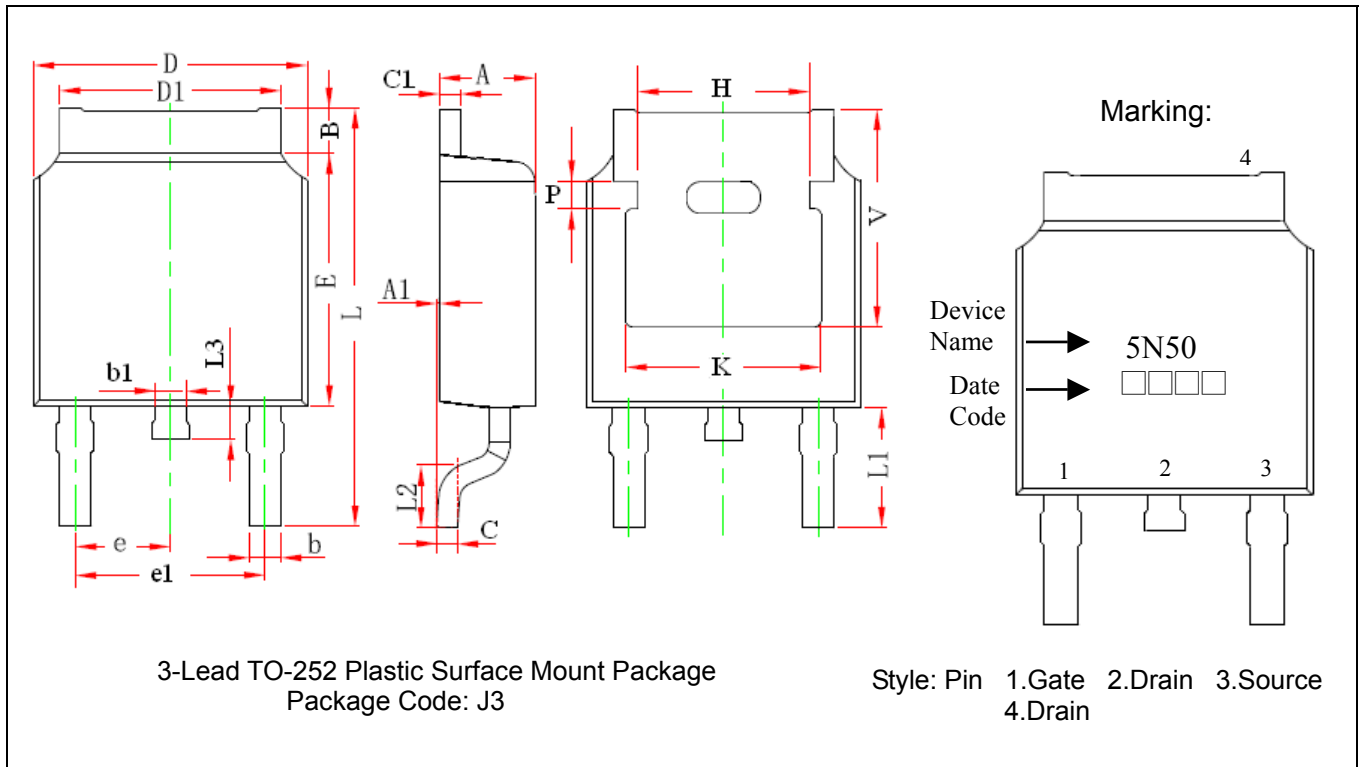
Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow


Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate ($T_{s\max}$ to T_p)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min($T_{s\min}$)	100°C	150°C
-Temperature Max($T_{s\max}$)	150°C	200°C
-Time($t_{s\min}$ to $t_{s\max}$)	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T_L)	183°C	217°C
- Time (t_L)	60-150 seconds	60-150 seconds
Peak Temperature(T_p)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(t_p)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

TO-252 Dimension


DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.087	0.094	2.200	2.400	e	0.086	0.094	2.186	2.386
A1	0.000	0.005	0.000	0.127	e1	0.172	0.188	4.372	4.772
B	0.039	0.048	0.990	1.210	H	0.163	REF	4.140	REF
b	0.026	0.034	0.660	0.860	K	0.190	REF	4.830	REF
b1	0.026	0.034	0.660	0.860	L	0.386	0.409	9.800	10.400
C	0.018	0.023	0.460	0.580	L1	0.114	REF	2.900	REF
C1	0.018	0.023	0.460	0.580	L2	0.055	0.067	1.400	1.700
D	0.256	0.264	6.500	6.700	L3	0.024	0.039	0.600	1.000
D1	0.201	0.215	5.100	5.460	P	0.026	REF	0.650	REF
E	0.236	0.244	6.000	6.200	V	0.211	REF	5.350	REF

Notes: 1.Controlling dimension: millimeters.

2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.

Material:

- Lead : Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.